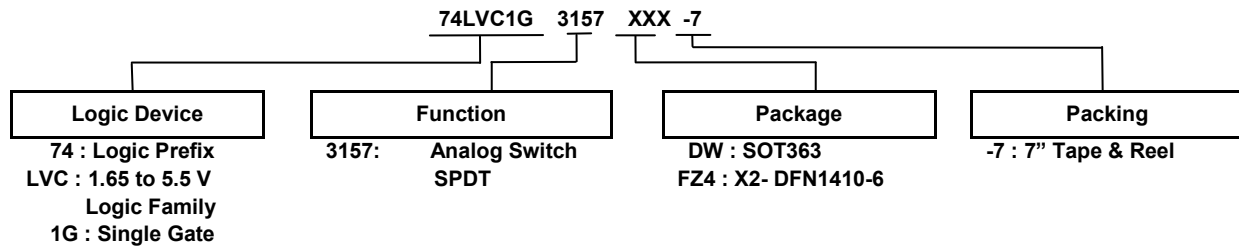


Ordering Information (Note 4)



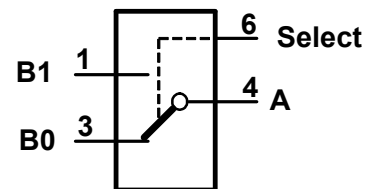
Device	Package Code	Package (Note 5)	Package Size	7" Tape and Reel (Note 6)	
				Quantity	Part Number Suffix
74LVC1G3157DW-7	DW	SOT363	2.0mm x 2.0mm x 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7
74LVC1G3157FZ4-7	FZ4	X2-DFN1410-6	1.4mm x 1.0mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7

Notes: 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.
5. Pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.
6. The taping orientation is located on our website at <https://www.diodes.com/assets/Packaging-Support-Docs/ap02007.pdf>.

Pin Descriptions

Pin Name	Description
B1	Selectable Data I/O
GND	Ground
B0	Selectable Data I/O
A	Common Data I/O
V _{CC}	Supply Voltage
Select	Selection Pin

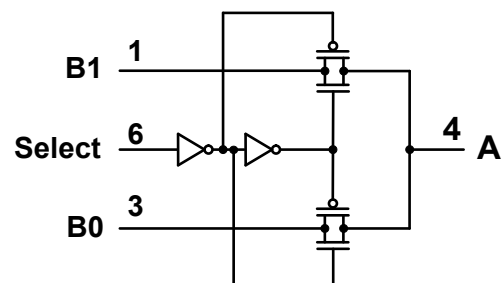
Logic Diagram



Function Table

Select	Status
H	B1 connected to A; B0 high impedance
L	B0 connected to A; B1 high impedance

Simplified Schematic



Absolute Maximum Ratings (Note 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V_{CC}	Supply Voltage Range	-0.5 to 6.5	V
V_{IN}	Input Voltage Range Applicable to Select Pin	-0.5 to 6.5	V
V_{SW}	Voltage Range Applicable to B0, B1, and A Pins	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	Input Clamp Current $V_I < 0$ Applicable to Select Pin	-50	mA
I_{IO}	Continuous Current Applicable to B0, B1, and A Pins	± 50	mA
I_{CC}, I_{GND}	Continuous current through V_{CC} or GND	± 100	mA
T_J	Operating Junction Temperature	-40 to +150	°C
T_{STG}	Storage Temperature	-65 to +150	°C

Note: 7. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions

Symbol	Parameter		Min	Max	Unit
V_{CC}	Operating Voltage	Operating	1.65	5.5	V
V_{IN}	Select Input Voltage		0	5.5	V
V_{SW}	Switch Voltage (applicable to pins B0, B1, A)		-0.2	V_{CC}	V
$\Delta t / \Delta V$	Input Transition Rise or Fall Rate – Select Pin	$V_{CC} = 1.65$ to $2.7V$	-	20	ns/V
		$V_{CC} = 2.7V$ to $5.5V$	-	10	
T_A	Operating Free-Air Temperature	-	-40	+125	°C

Electrical Characteristics (All typical values are at, $T_J = +25^\circ\text{C}$)

Symbol	Parameter	Test Condition	V_{CC} (V)	$T_A = -40$ to $+85^\circ\text{C}$			$T_A = -40$ to $+125^\circ\text{C}$		Unit
				Min	Typical (Note 8)	Max	Min	Max	
V_{IH}	High Level Input Voltage Select Pin	-	1.65 to 1.95	$0.65V_{CC}$	-	-	$0.65V_{CC}$	-	V
			2.3 to 2.7	1.7	-	-	1.7	-	
			3 to 3.6	2.0	-	-	2.0	-	
			4.5 to 5.5	$0.7V_{CC}$	-	-	$0.7V_{CC}$	-	
V_{IL}	Low Level Input Voltage Select Pin	-	1.65 to 1.95	-	-	$0.35V_{CC}$	-	$0.35V_{CC}$	V
			2.3 to 2.7	-	-	0.7	-	0.7	
			3 to 3.6	-	-	0.8	-	0.8	
			4.5 to 5.5	-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	
I_{IN}	Input Leakage Current Select Pin	$0 \leq \text{Select} \leq 5.5\text{V}$	0 to 5.5	-	± 0.05	± 1	-	± 10	μA
$I_{S(OFF)}$	OFF State Leakage Current	$0\text{V} \leq A, B_n \leq V_{CC}$ Figure 1	1.65 to 5.5	-	± 0.05	± 1	-	± 10	μA
$I_{S(ON)}$	ON State Leakage Current	$0\text{V} \leq A, B_n \leq V_{CC}$ Figure 2	1.65 to 5.5	-	± 0.05	± 1	-	± 10	μA
$I_{S(ON)}$	ON State Leakage Current	$-0.1\text{V} \leq A, B_n \leq V_{CC}$ Figure 2	1.65 to 5.5	-	± 0.05	± 2	-	± 20	μA
I_{CC}	Quiescent Supply Current	Select = V_{CC} or GND $A, B_n = V_{CC}$ or GND $I_{OUT} = 0$	5.5	-	1.0	10	-	40	μA
ΔI_{CC}	Additional Supply Current	Select = $V_{CC} - 0.6\text{V}$ $A, B_n = V_{CC}$ or GND $I_{OUT} = 0$	5.5	-	30	500	-	5,000	μA
C_I	Input Capacitance Select Pin	-	3.3	-	2.5	-	-	-	pF
$C_{S(OFF)}$	OFF State Capacitance	Select = V_{CC} or GND $A, B_n = V_{CC}$ or GND $I_{OUT} = 0$	3.3	-	6.0	-	-	-	pF
$C_{S(ON)}$	ON State Capacitance	Select = V_{CC} or GND $A, B_n = V_{CC}$ or GND $I_{OUT} = 0$	3.3	-	18	-	-	-	pF

Note: 8. Typical performance information is included in figures 11 to 34 on pages 11 to 14.

Electrical Characteristics (All typical values are at $T_J = +25^\circ\text{C}$)

Symbol	Parameter	Test Condition (Note 9)	V_{CC} (V)	$T_A = -40$ to $+85^\circ\text{C}$			$T_A = -40$ to $+125^\circ\text{C}$		Unit
				Min	Typ	Max	Min	Max	
R_{ON}	ON Resistance	$V_I = 0\text{V}, I_O = 4\text{mA}$	1.65	-	12.5	18	-	27	Ω
		$V_I = 1.65\text{V}, I_O = -4\text{mA}$		-	14	18	-	35	
		$V_I = 0\text{V}, I_O = 8\text{mA}$	2.3	-	9.0	16	-	24	
		$V_I = 2.3\text{V}, I_O = -8\text{mA}$		-	9.0	16	-	30	
		$V_I = 0\text{V}, I_O = 12\text{mA}$	2.7	-	8.0	14	-	21	
		$V_I = 2.7\text{V}, I_O = -12\text{mA}$		-	8.0	14	-	27	
		$V_I = 0\text{V}, I_O = 24\text{mA}$	3.0	-	7.0	12	-	18	
		$V_I = 3.0\text{V}, I_O = -24\text{mA}$		-	7.0	12	-	23	
		$V_I = 0\text{V}, I_O = 32\text{mA}$	4.5	-	5.5	10	-	15	
		$V_I = 2.7\text{V}, I_O = -32\text{mA}$		-	6.0	12	-	17	
		$V_I = 4.5\text{V}, I_O = -32\text{mA}$		-	5.5	10	-	15	
R_{RANGE}	On Resistance Over Signal Range	$I_A = 4\text{mA}, 0 \leq V_{BN} \leq V_{CC}$	1.65	-	34	130	-	195	Ω
		$I_A = 8\text{mA}, 0 \leq V_{BN} \leq V_{CC}$	2.3	-	5	30	-	45	
		$I_A = 12\text{mA}, 0 \leq V_{BN} \leq V_{CC}$	2.7	-	4	25	-	38	
		$I_A = 24\text{mA}, 0 \leq V_{BN} \leq V_{CC}$	3.0	-	7.8	20	-	30	
		$I_A = 32\text{mA}, 0 \leq V_{BN} \leq V_{CC}$	4.5	-	6.2	15	-	23	
ΔR_{ON}	On Resistance Match Between Channels (Note 10)	$I_A = -4\text{mA}, V_{BN} = 1.15\text{V}$	1.65	-	0.25	-	-	-	Ω
		$I_A = -8\text{mA}, V_{BN} = 1.6\text{V}$	2.3	-	0.25	-	-	-	
		$I_A = -12\text{mA}, V_{BN} = 1.9\text{V}$	2.7	-	0.25	-	-	-	
		$I_A = -24\text{mA}, V_{BN} = 2.1$	3.0	-	0.25	-	-	-	
		$I_A = -32\text{mA}, V_{BN} = 3.15$	4.5	-	0.25	-	-	-	
R_{flat}	On Resistance Flatness (Note 11)	$I_A = -4\text{mA}, 0 \leq V_{BN} \leq V_{CC}$	1.65	-	26	110	-	150	Ω
		$I_A = -8\text{mA}, 0 \leq V_{BN} \leq V_{CC}$	2.3	-	5.0	26	-	105	
		$I_A = -24\text{mA}, 0 \leq V_{BN} \leq V_{CC}$	2.7	-	3.5	16	-	35	
		$I_A = -24\text{mA}, 0 \leq V_{BN} \leq V_{CC}$	3.3	-	2.0	9	-	15	
		$I_A = -32\text{mA}, 0 \leq V_{BN} \leq V_{CC}$	5.0	-	1.5	4	-	8	

Note: 9. Switch resistance test is measured per Figure 3.

10. ΔR_{ON} is measured at identical V_{CC} , temperature and voltage levels.

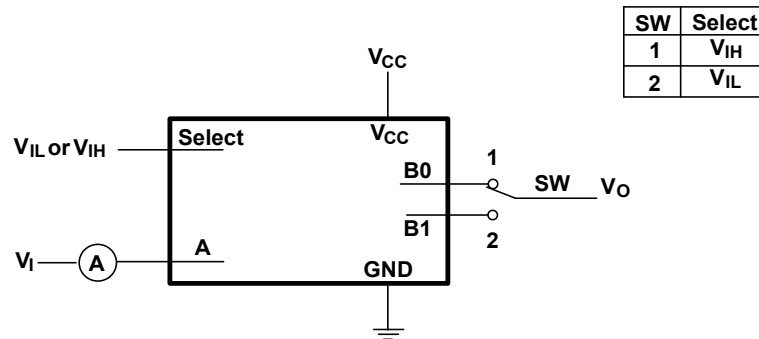
11. Flatness is defined as the difference between the maximum and minimum of ON resistance measured at identical V_{CC} and temperature.

Switching Characteristics

Symbol	Parameter	Test Condition	V _{CC} Volts	T _A = -40 to +85°C			T _A = -40 to +125°C		Unit	Figure Number
				Min	Typ	Max	Min	Max		
t _{PHL} t _{PLH}	Propagation Delay A to B _n	V _I = OPEN (Note 12)	1.65 to 1.95	-	-	2.0	-	3.0	ns	Figure 4
			2.3 to 2.7	-	-	1.2	-	2.0		
			2.7	-	-	1.0	-	1.5		
			3.0 to 3.6	-	-	0.8	-	1.5		
			4.5 to 5.5	-	-	0.6	-	1.0		
t _{PZL} t _{PZH}	Output Enable Time Switch to B _n	V _I = 2 x V _{CC} for t _{PZL} V _I = 0V for t _{PZH} (Note 13)	1.65 to 1.95	1.0	8.7	14.0	1.0	14.0	ns	Figure 4
			2.3 to 2.7	1.0	5.3	7.5	1.0	7.5		
			2.7	1.0	4.9	6.0	1.0	6.0		
			3.0 to 3.6	0.5	4.0	5.5	0.5	5.5		
			4.5 to 5.5	0.5	3.0	4.0	0.5	4.0		
t _{PLZ} t _{PHZ}	Output Disable Time Switch to B _n	V _I = 2 x V _{CC} for t _{PLZ} V _I = 0V for t _{PHZ} (Note 13)	1.65 to 1.95	2.5	6.0	8.5	2.5	8.5	ns	Figure 4
			2.3 to 2.7	2.0	4.4	8.2	2.0	8.2		
			2.7	1.5	4.2	8.0	1.5	8.0		
			3.0 to 3.6	1.5	3.6	7.8	1.5	7.8		
			4.5 to 5.5	0.8	2.9	7.5	0.8	7.5		
t _{B-M}	Break Before Make Time (Note 9)	-	1.65 to 1.95	0.5	-	-	0.5	-	ns	Figure 5
			2.3 to 2.7	0.5	-	-	0.5	-		
			2.7	0.5	-	-	0.5	-		
			3.0 to 3.6	0.5	-	-	0.5	-		
			4.5 to 5.5	0.5	-	-	0.5	-		
Q	Charge Injection (Note 9)	C _L = 0.1 nF, V _{GEN} = 0V R _{GEN} = 0 Ω	5.0	-	7.0	-	-	-	pC	Figure 6
			3.3	-	3.0	-	-	-		
QIRR	Off Isolation (Note 11)	R _L = 50 Ω, f = 10MHz	1.65 ~ 5.5	-	-42	-	-	-	dB	Figure 7
Xtalk	Crosstalk	R _L = 50 Ω, f = 10MHz	1.65 ~ 5.5	-	-42	-	-	-	dB	Figure 8
BW	-3dB Bandwidth	R _L = 50 Ω	1.65 ~ 5.5	-	300	-	-	-	MHz	Figure 9
THD	Total Harmonic Distortion (Note 9)	R _L = 600 Ω, 0.5 V _{P-P} , f = 600Hz to 20kHz	5.0	-	0.1	-	-	-	%	Figure 10

- Notes:
- Due to the symmetry of the part, the direction of the propagation delay applies to either direction A to B_n or B_n to A. Propagation time is the calculated RC time constant of the typical ON resistance of the switch and the specified load capacitance when capacitance when driven by an ideal voltage source.
 - The Switch signal enable and disables time are the same for B_n and A if they are reversed at input and output.

Parameter Measurement Information



Condition 1: $V_I = \text{GND}, V_O = V_{CC}$

Condition 2: $V_I = V_{CC}, V_O = \text{GND}$

Figure 1 OFF –State Leakage Current Test

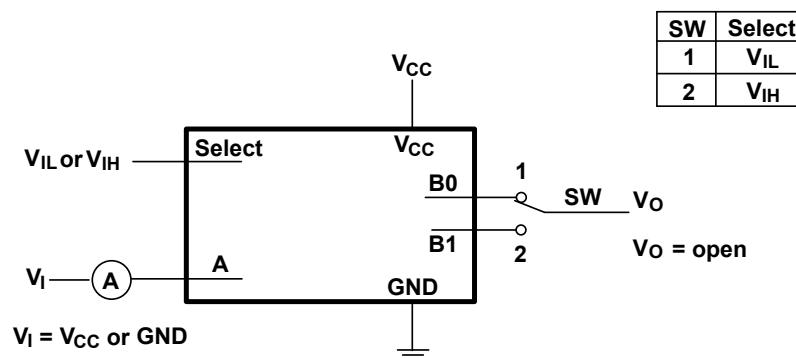


Figure 2 ON –State Leakage Current Test

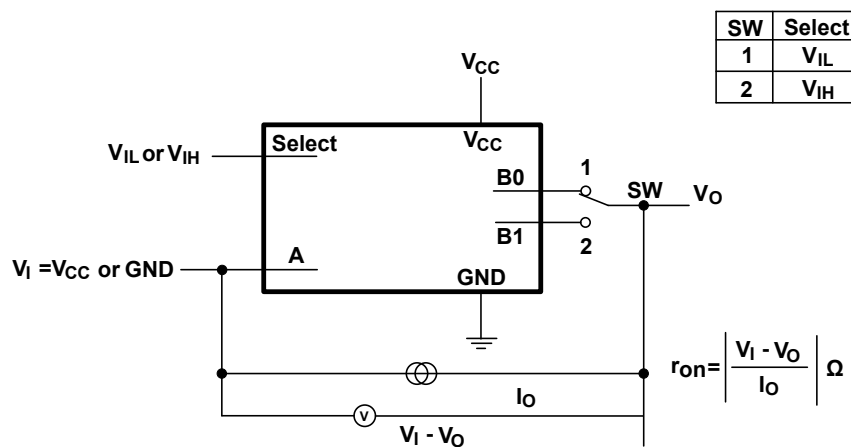
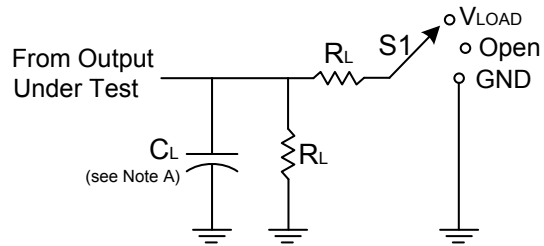


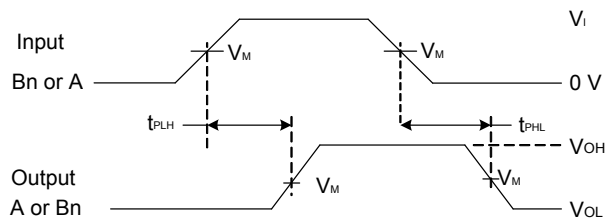
Figure 3 ON State Resistance Test

Parameter Measurement Information (Notes 15-19)

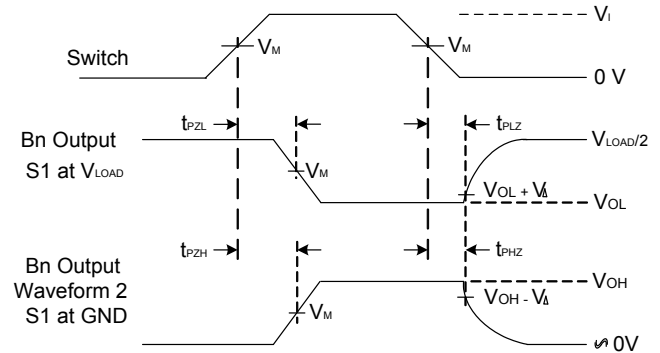


TEST	S1	R_L
t_{PLH}/t_{PHL}	Open	500 Ω
t_{PLZ}/t_{PZL}	Vload	500 Ω
t_{PHZ}/t_{PZH}	GND	500 Ω

V_{CC}	Inputs		V_M	V_{LOAD}	C_L (Note 14)	V_{Δ}
	V_I	t_r/t_f				
$1.8V \pm 0.15V$	V_{CC}	$\leq 2ns$	$V_{CC}/2$	$2 \times V_{CC}$	50pF	0.1V
$2.5V \pm 0.2V$	V_{CC}	$\leq 2ns$	$V_{CC}/2$	$2 \times V_{CC}$	50pF	0.1V
$3.3V \pm 0.3V$	V_{CC}	$\leq 2.5ns$	$V_{CC}/2$	$2 \times V_{CC}$	50pF	0.1V
$5V \pm 0.5V$	V_{CC}	$\leq 2.5ns$	$V_{CC}/2$	$2 \times V_{CC}$	50pF	0.1V



Voltage Waveform Propagation Delay Times



Voltage Waveform Enable and Disable Times

Figure 4 Load Circuit and Voltage Waveforms

- Notes:
- Includes test lead and test apparatus capacitance.
 - All pulses are supplied at pulse repetition rate $\leq 10MHz$.
 - Inputs are measured separately one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{EN} .
 - t_{PLH} and t_{PHL} are the same as t_{PD} .

Parameter Measurement Information (continued)

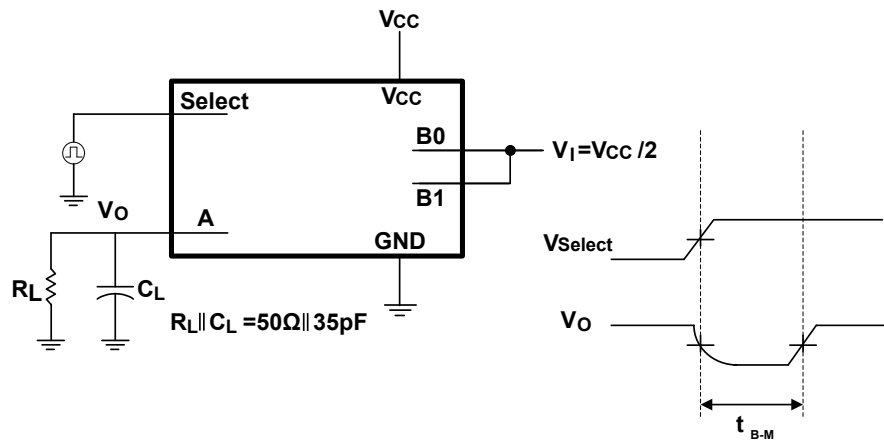


Figure 5 Break before Make Timing Test

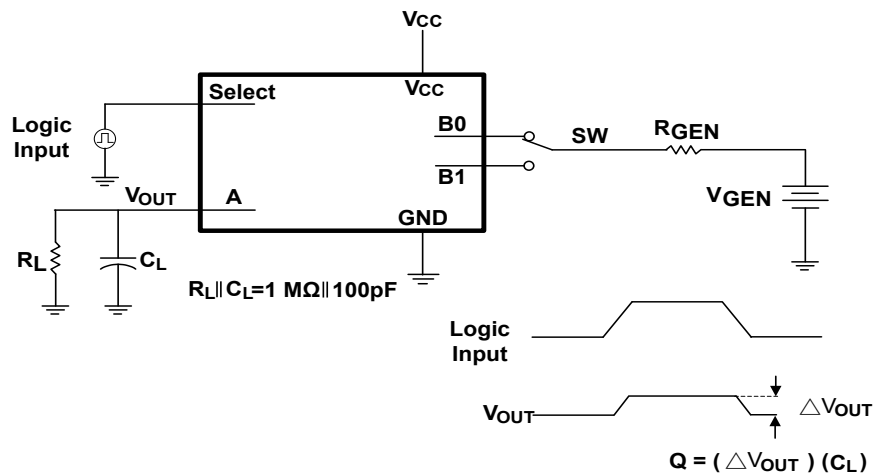


Figure 6 Charge Injection

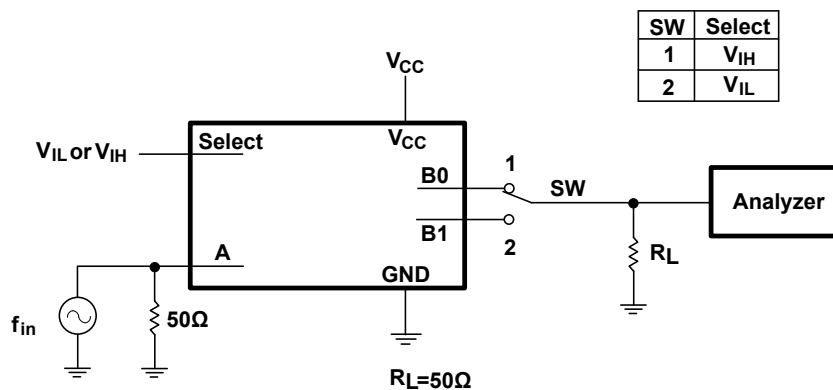


Figure 7 OFF Isolation

Parameter Measurement Information (continued)

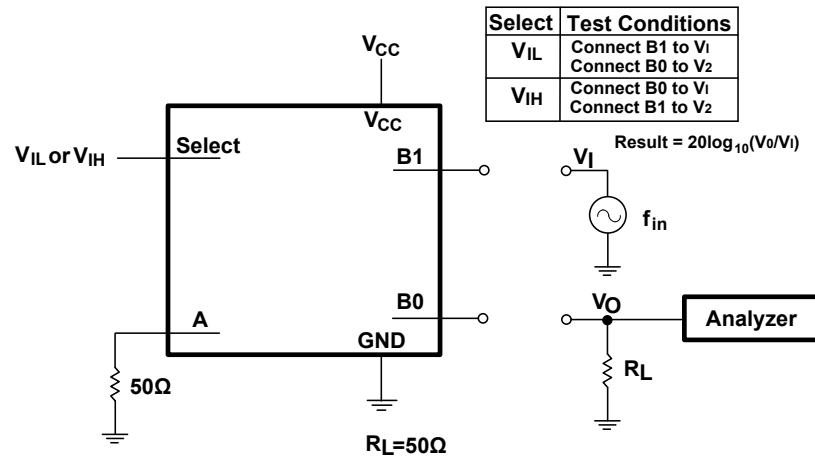


Figure 8 Cross Talk

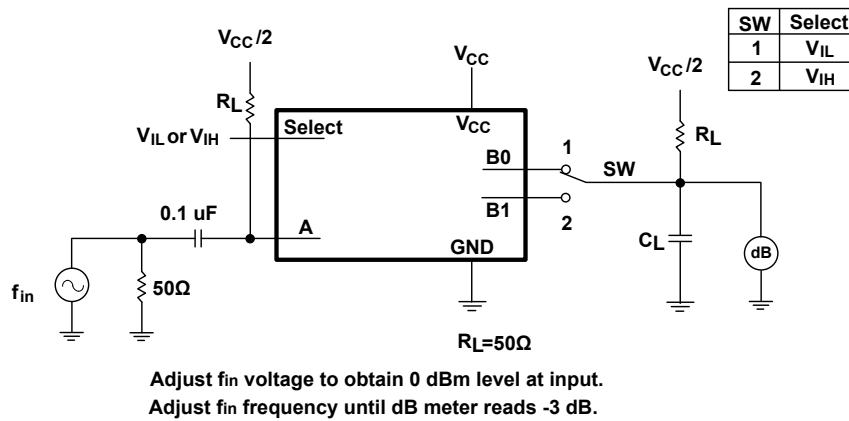


Figure 9 Bandwidth

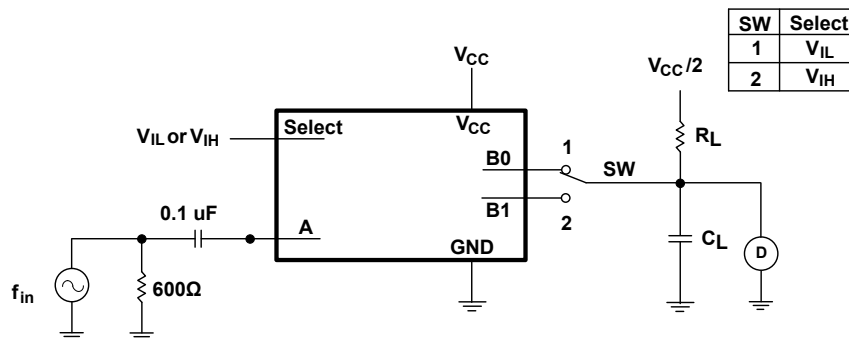


Figure 10 THD

Typical Performance Characteristics

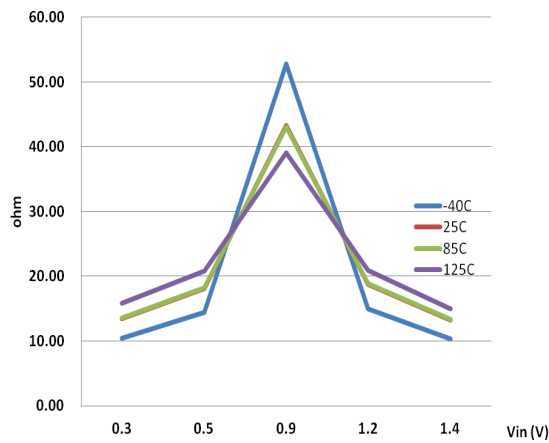


Figure 11 ON state Resistance $V_{CC} = 1.65\text{ V}$; $I_{Bn} = 4\text{ ma}$

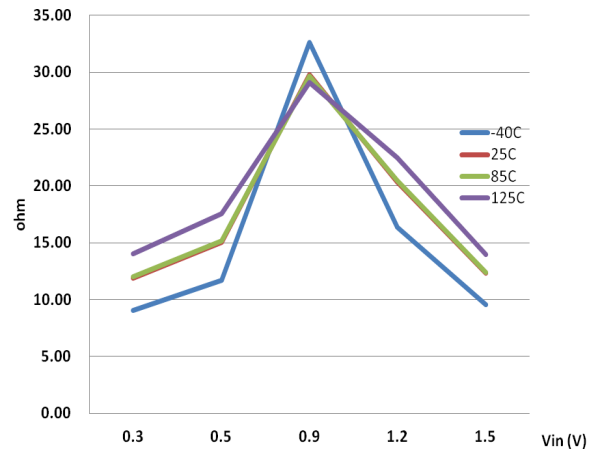


Figure 12 ON state Resistance $V_{CC} = 1.8\text{ V}$; $I_{Bn} = 4\text{ ma}$

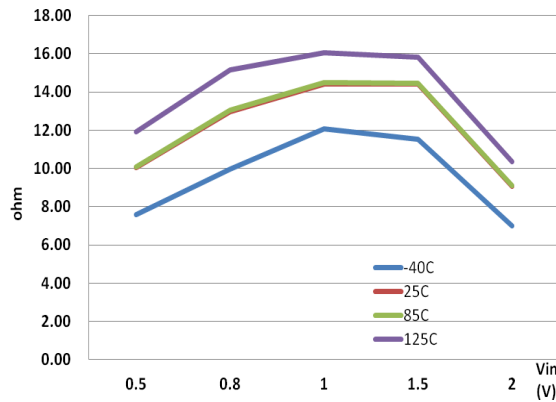


Figure 13 ON state Resistance $V_{CC} = 2.3\text{ V}$; $I_{Bn} = 8\text{ ma}$

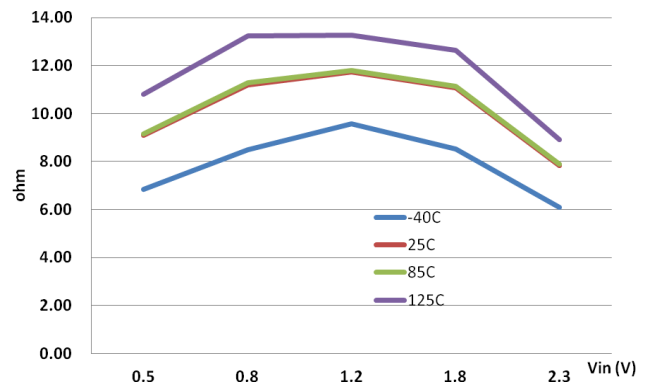


Figure 14 ON state Resistance $V_{CC} = 2.5\text{ V}$; $I_{Bn} = 8\text{ ma}$

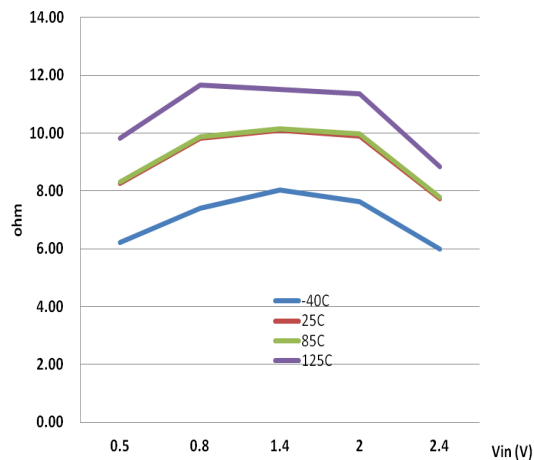


Figure 15 ON state Resistance $V_{CC} = 2.7\text{ V}$; $I_{Bn} = 12\text{ ma}$

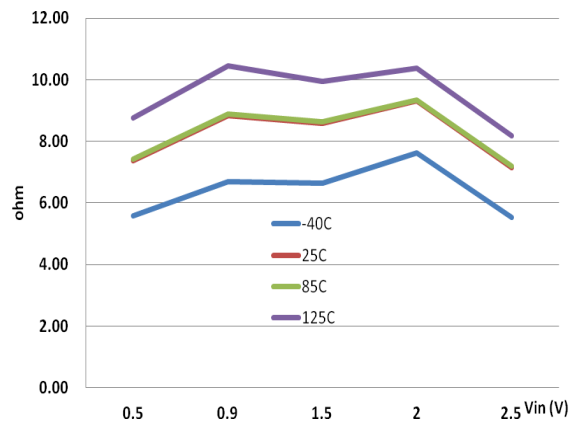


Figure 16 ON state Resistance $V_{CC} = 3\text{ V}$; $I_{Bn} = 24\text{ ma}$

Typical Performance Characteristics (continued)

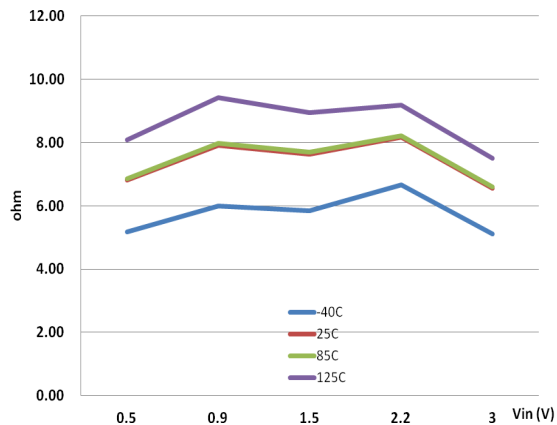


Figure 17 ON state Resistance Vcc = 3.3 V; IBn = 24ma

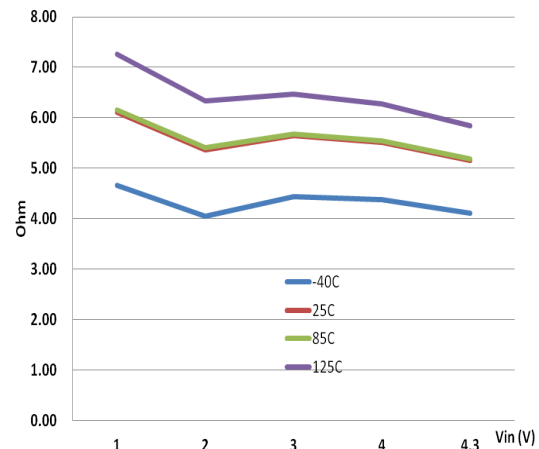


Figure 18 ON state Resistance Vcc = 4.5 V; IBn = 32ma

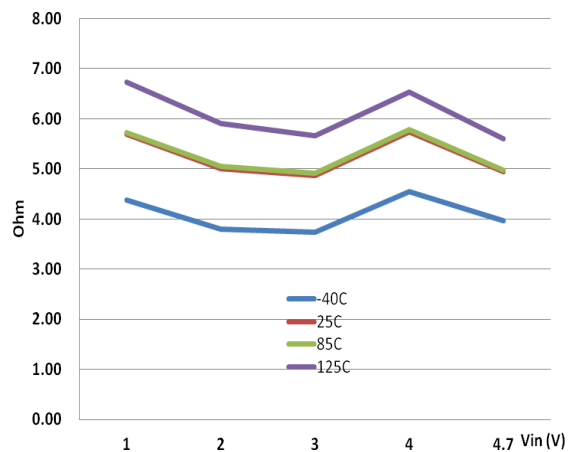


Figure 19 ON state Resistance Vcc = 5.5 V; IBn = 32ma

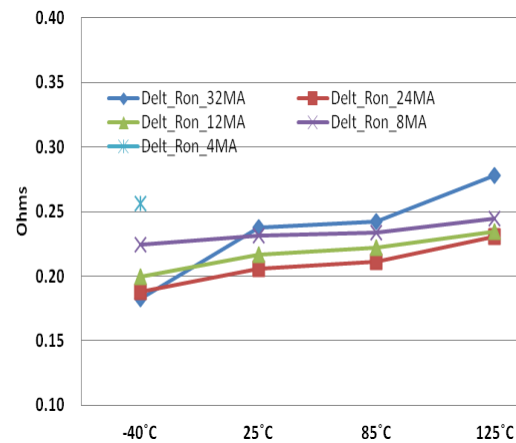


Figure 20 ΔRon-Resistance Match Between Channels

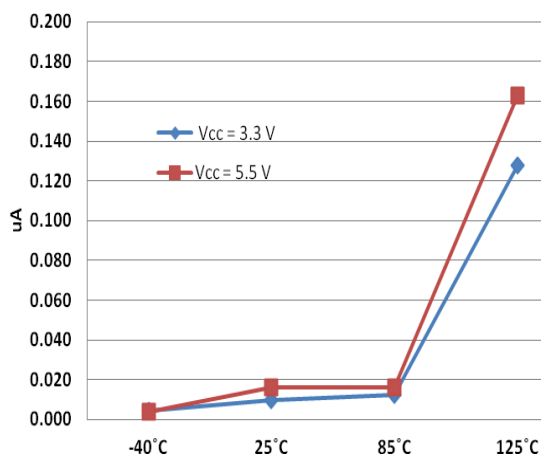


Figure 21 IS(OFF) OFF state leakage VIN = 0 V

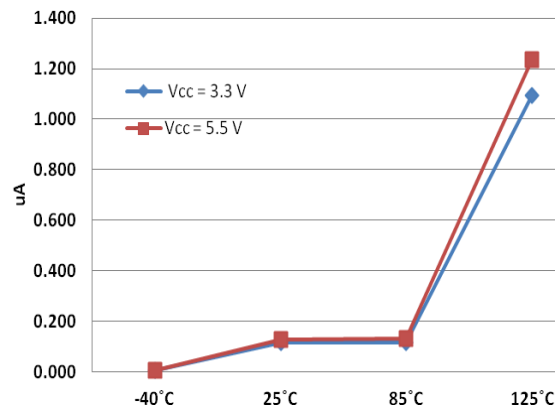


Figure 22 IS(OFF) OFF state leakage VIN = -0.1 V

Typical Performance Characteristics (continued)

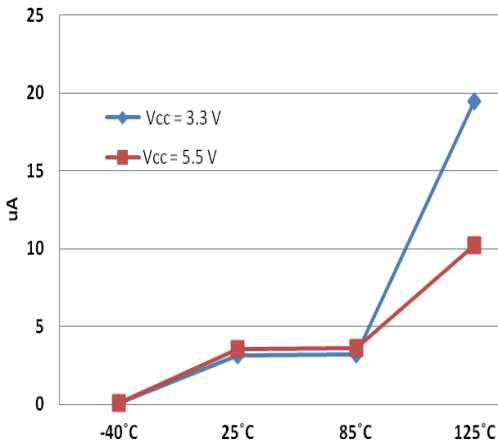


Figure 23 $I_{S(OFF)}$ OFF state leakage $V_{IN} = -0.2\text{ V}$

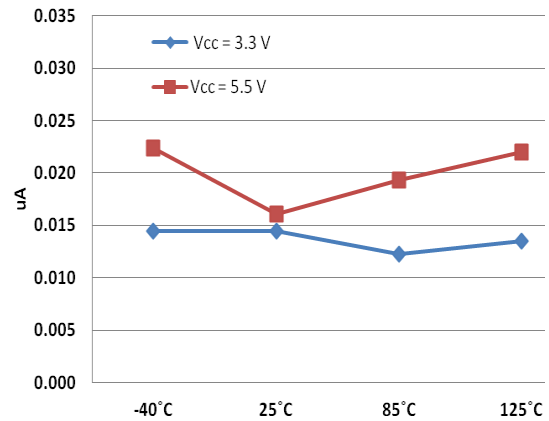


Figure 24 $I_{S(ON)}$ ON state leakage $V_{IN} = 0\text{ V}$

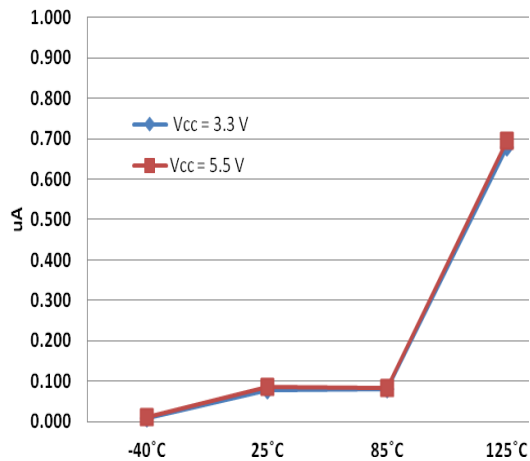


Figure 25 $I_{S(ON)}$ ON state leakage $V_{IN} = -0.1\text{ V}$

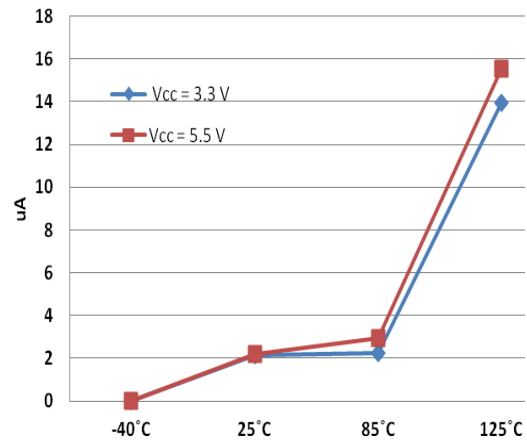


Figure 26 $I_{S(ON)}$ ON state leakage $V_{IN} = -0.2\text{ V}$

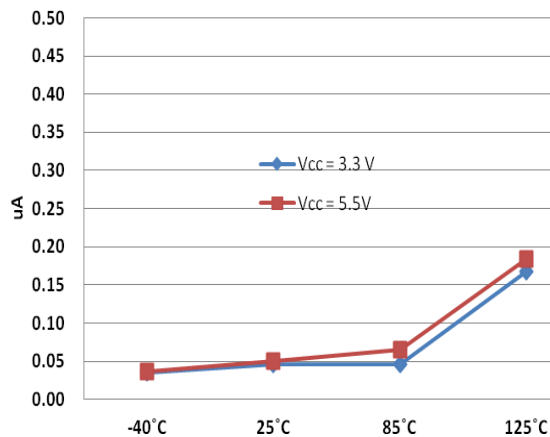


Figure 27 I_{CC} versus Temperature

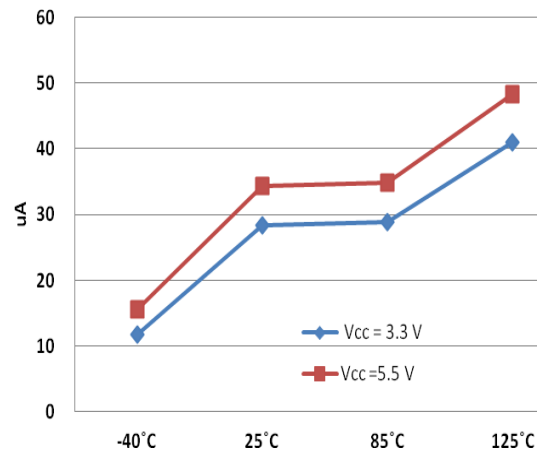


Figure 28 ΔI_{CC} versus Temperature

Typical Performance Characteristics (continued)

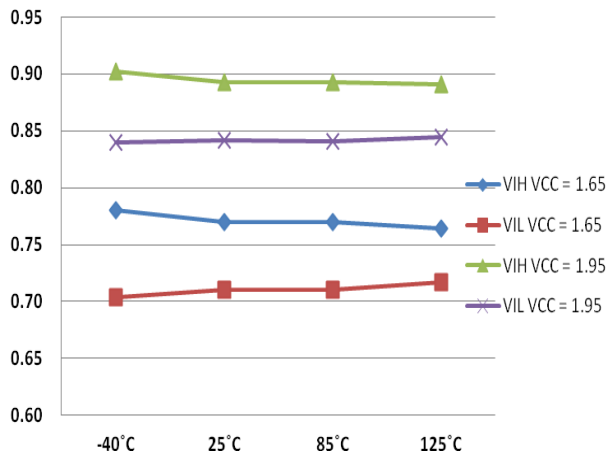


Figure 29 V_{IH} , V_{IL} , Hysteresis $V_{CC} = 1.65$ V and $V_{CC} = 1.95$ V

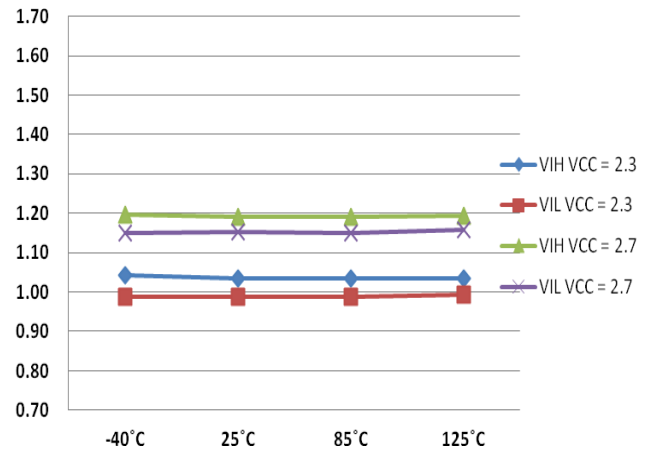


Figure 30 V_{IH} , V_{IL} , Hysteresis $V_{CC} = 2.3$ V and $V_{CC} = 2.7$ V

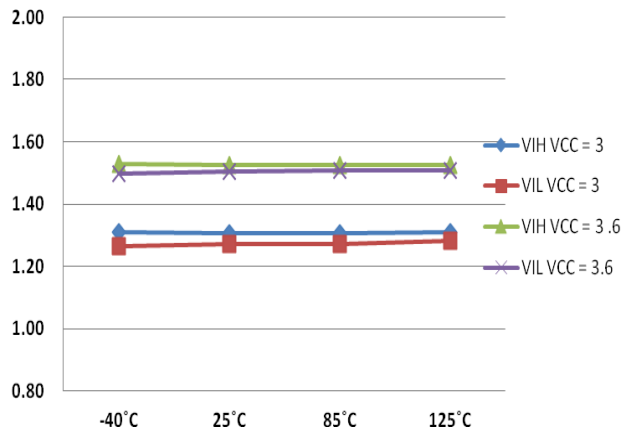


Figure 31 V_{IH} , V_{IL} , Hysteresis $V_{CC} = 3$ V and $V_{CC} = 3.3$ V

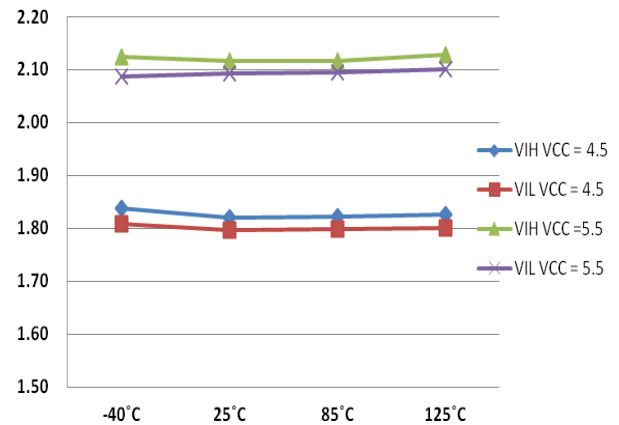
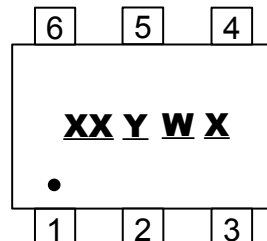


Figure 32 V_{IH} , V_{IL} , Hysteresis $V_{CC} = 4.5$ V and $V_{CC} = 5.5$ V

Marking Information

(1) SOT363

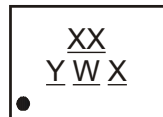


XX : Identification code
Y : Year 0~9
W : Week : A~Z : 1~26 week;
 a~z : 27~52 week; z represents
 52 and 53 week
X : A~Z : Internal Code

Part Number	Package	Identification Code
74LVC1G3157DW	SOT363	J7

(2) X2-DFN1410-6

(Top View)



XX : Identification Code
Y : Year 0~9
W : Week : A~Z : 1~26 week;
 a~z : 27~52 week;
 z represents 52 and 53 week
X : A~Z : Internal Code

Part Number	Package	Identification Code
74LVC1G3157FZ4	X2-DFN1410-6	J7

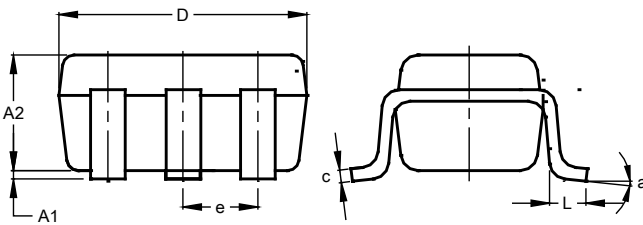
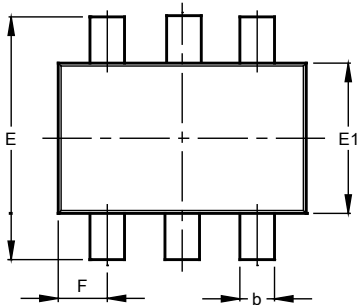
Package Characteristics (All typical values are at $V_{CC} = 3.3V$, $T_A = +25^{\circ}C$)

Symbol	Parameter	Test Conditions	V_{CC}	Min	Typ.	Max	Unit
θ_{JA}	Thermal Resistance Junction-to-Ambient	SOT363	(Note 20)	-	371	-	$^{\circ}C/W$
		X2-DFN1410-6		-	460	-	
θ_{JC}	Thermal Resistance Junction-to-Case	SOT363	(Note 20)	-	143	-	$^{\circ}C/W$
		X2-DFN1410-6		-	265	-	

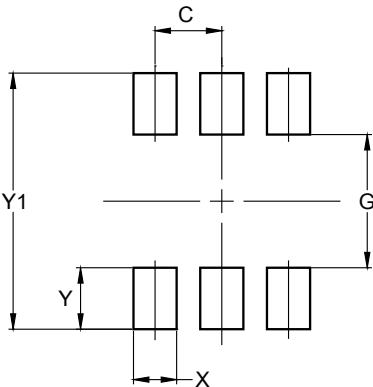
Note: 20. Test condition SOT363, and X2-DFN1410-6: Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.

SOT363 Package Outline Dimensions and Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



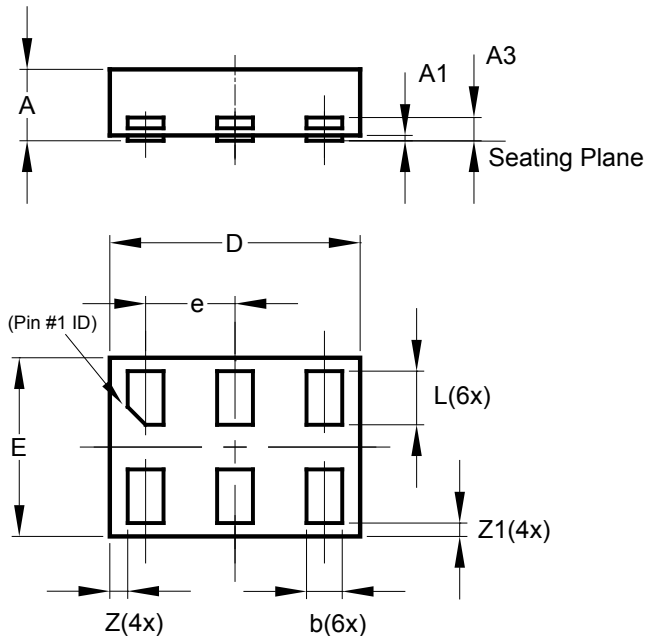
SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			



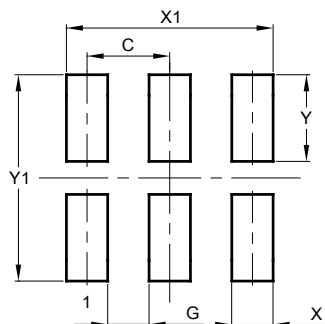
Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

X2-DFN1410-6 Package Outline Dimensions and Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



X2-DFN1410-6			
Dim	Min	Max	Typ
A	—	0.40	0.39
A1	0.00	0.05	0.02
A3	—	—	0.13
b	0.15	0.25	0.20
D	1.35	1.45	1.40
E	0.95	1.05	1.00
e	—	—	0.50
L	0.25	0.35	0.30
Z	—	—	0.10
Z1	0.045	0.105	0.075
All Dimensions in mm			



Dimensions	Value (in mm)
C	0.500
G	0.250
X	0.250
X1	1.250
Y	0.525
Y1	1.250

Mechanical Data

SOT363

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ^(e3)
- Weight: 0.0064 grams (Approximate)

X2-DFN1410-6

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - NiPdAu Nickel Palladium Gold, Solderable per MIL-STD-202, Method 208 ^(e4)
- Weight: 0.002 grams (Approximate)

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